



#### **SINGLE 3 INPUT POSITIVE AND GATE**

## **Description**

The 74LVC1G11 is a single 3-input positive AND gate with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down.

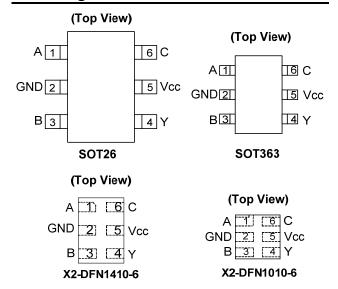
The gate performs the positive Boolean function:

$$Y = A \bullet B \bullet C$$
 or  $Y = \overline{A + B + C}$ 

## **Features**

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs Accept up to 5.5V
- ESD Protection Exceeds JESD 22:
  - 200-V Machine Model (A115-A)
  - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class I
- Range of Package Options
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Pin Assignments**



## **Applications**

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
  - PCs, networking, notebooks, Netbooks, PDAs
  - Computer Peripherals, Hard Drives, CD/DVD ROM
  - TV, DVD, DVR, Set Top Box
  - Cell Phones, Personal Navigation / GPS
  - MP3 players ,Cameras, Video Recorders

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

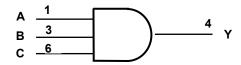
Click here for ordering information, located at the end of datasheet



# **Pin Descriptions**

Pin Name	Function
Α	Data Input
GND	Ground
В	Data Input
Y	Data Output
Vcc	Supply Voltage
С	Data Input

# **Logic Diagram**



## **Function Table**

	Inputs					
Α	В	С	Υ			
Н	Н	Н	Н			
L	Χ	Х	L			
Х	L	Х	L			
Х	Х	L	L			

## Absolute Maximum Ratings (Note 4) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
lık	Input Clamp Current V <sub>I</sub> <0	-50	mA
lok	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
I <sub>CC MAX CONT</sub>	Continuous current through Vcc or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



# Recommended Operating Conditions (Note 5) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol		Parameter	Min	Max	Unit
\/	Operating Voltage	Operating	1.65	5.5	V
Vcc	Operating Voltage	Data Retention Only	1.5		V
		V <sub>CC</sub> = 1.65V to 1.95V	0.65 X V <sub>CC</sub>		
\/	High-Level Input Voltage	V <sub>CC</sub> = 2.3V to 2.7V	1.7		V
$V_{IH}$	High-Level Input Voltage	V <sub>CC</sub> = 3V to 3.6V	2		V
		V <sub>CC</sub> = 4.5V to 5.5V	0.7 X V <sub>CC</sub>		
		V <sub>CC</sub> = 1.65V to 1.95V		0.35 X V <sub>CC</sub>	
	Law Lavel Innut Valtage	V <sub>CC</sub> = 2.3V to 2.7V		0.7	V
$V_{IL}$	Low-Level Input Voltage	V <sub>CC</sub> = 3V to 3.6V		0.8	V
		V <sub>CC</sub> = 4.5V to 5.5V		0.3 X V <sub>CC</sub>	
VI	Input Voltage	•	0	5.5	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.65V		-4	
		V <sub>CC</sub> = 2.3V			-8
I <sub>OH</sub>	High-Level Output Current	V - 2V		-16	mA
		V <sub>CC</sub> = 3V		-24	
		V <sub>CC</sub> = 4.5V		-32	
		V <sub>CC</sub> = 1.65V		4	
		$V_{CC} = 2.3V$		8	
$I_{OL}$	Low-Level Output Current	V <sub>CC</sub> = 3V		16	mA
		VCC - 3V		24	
		V <sub>CC</sub> = 4.5V		32	
		$V_{CC}$ = 1.8V ± 0.15V, 2.5V ± 0.2V		20	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V
	Kale	$V_{CC} = 5V \pm 0.5V$		5	
T <sub>A</sub>	Operating Free-Air Temperature		-40	+125	°C

Note:

5. Unused inputs should be held at  $V_{\mbox{\footnotesize CC}}$  or Ground.



# **Electrical Characteristics** $T_A = -40$ °C to +85°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> - 0.1			
		I <sub>OH</sub> = -4mA	1.65V	1.2			
	High Lavel Output Valtage	I <sub>OH</sub> = -8mA	2.3V	1.9			1/
VoH	High-Level Output Voltage	I <sub>OH</sub> = -16mA	2)./	2.4			V
		I <sub>OH</sub> = -24mA	3V	2.3			
		I <sub>OH</sub> = -32mA	4.5V	3.8			
		I <sub>OL</sub> = 100μA	1.65V to 5.5V			0.1	
	Land Code AVallage	I <sub>OL</sub> = 4mA	1.65V			0.45	
\ /		I <sub>OL</sub> = 8mA	2.3V			0.3	V
$V_{OL}$	Low-Level Output Voltage	I <sub>OL</sub> = 16mA	2)./			0.4	V
		I <sub>OL</sub> = 24mA	3V			0.55	
		I <sub>OL</sub> = 32mA	4.5V			0.55	
I	Input Current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5V			± 5	μΑ
l <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 5.5V	0			± 10	μΑ
Icc	Supply Current	$V_1 = 5.5V \text{ of GND}, I_0 = 0$	1.65V to 5.5V			10	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> –0.6V	3V to 5.5V			500	μA

# **Electrical Characteristics** $T_A = -40$ °C to +125°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Тур	Max	Unit
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> - 0.1			
		$I_{OH} = -4mA$	1.65V 0.95				
\ <u>'</u>	High-Level Output Voltage	I <sub>OH</sub> = -8mA	2.3V	1.7			V
V <sub>OH</sub>	High-Level Output voltage	I <sub>OH</sub> = -16mA	3V	1.9			v
		I <sub>OH</sub> = -24mA	30	2.0			
		I <sub>OH</sub> = -32mA	4.5V	3.4			
		I <sub>OL</sub> = 100μA	1.65V to 5.5V			0.1	
	Low-Level Output Voltage	I <sub>OL</sub> = 4mA	1.65V			0.70	
N/		I <sub>OL</sub> = 8mA	2.3V			0.45	V
V <sub>OL</sub>	Low-Level Output voltage	I <sub>OL</sub> = 16mA	- 3V			0.60	v
		I <sub>OL</sub> = 24mA	30			0.80	
		I <sub>OL</sub> = 32mA	4.5V			0.80	
I <sub>I</sub>	Input Current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5V			± 20	μΑ
I <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 5.5V	0			± 20	μΑ
Icc	Supply Current	$V_{I} = 5.5V$ of GND, $I_{O} = 0$	1.65V to 5.5V			40	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> –0.6 V	3V to 5.5V			5000	μA



## Package Characteristics (All typical values are at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
Cı	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF
		SOT26			204		
	Thermal Resistance Junction-	SOT363	(Note 6)		371		°C/W
$\theta_{JA}$	to-Ambient	X2-DFN1410-6	(Note 6)		430		C/VV
		X2-DFN1010-6			510		
		SOT26			52		
_	Thermal Resistance Junction-	SOT363	(Note 6)		143		°C/W
AlC	θ <sub>JC</sub> to-Case	X2-DFN1410-6	(Note 6)		190		C/VV
		X2-DFN1010-6			250		

Note:

## **Switching Characteristics**

 $T_A = -40$ °C to +85°C,  $C_L = 15$ pF (see Figure 1)

Parameter	From TO (OUTPUT		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V		Unit
	(iliput)	(0011-01)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	15.2	0.7	5.6	0.7	4.1	0.7	3.1	ns

## $T_A = -40$ °C to +85°C, $C_L = 30$ or 50pF (see Figure 2)

Parameter	From (Input)	TO (OUTPUT)	V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V V <sub>CC</sub> = ± 0.2V ± 0			V <sub>CC</sub> = 5V ± 0.5V		Unit	
	(mput)	(0011-01)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	17.2	0.7	6.2	0.7	4.9	0.7	3.5	ns

### $T_A = -40$ °C to +125°C, $C_L = 15$ pF (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		3.3V .3V	$V V_{CC} = 5V$ $\pm 0.5V$		Unit
	(IIIput)	(001701)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	18.3	0.7	6.7	0.7	4.9	0.7	3.7	ns

### $T_A = -40$ °C to +125°C, $C_L = 30$ or 50pF (see Figure 2)

Parameter	From (Input)	TO (OUTPUT)		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		3.3V .3V	V <sub>CC</sub> = 5V ± 0.5V		Unit
	(mpat)	(0011-01)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	20.7	0.7	7.5	0.7	5.9	0.7	4.2	ns

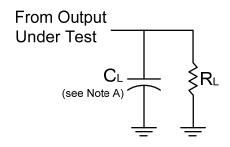
<sup>6.</sup> Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6 : Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



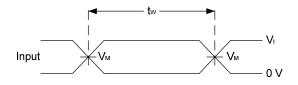
## Operating Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Parameter	Test Conditions	V <sub>CC</sub> = 1.8V Typ	V <sub>CC</sub> = 2.5V Typ	V <sub>CC</sub> = 3.3V Typ	V <sub>CC</sub> = 5V Typ	Unit
$C_{pd}$	Power dissipation capacitance	f = 10 MHz	17	18	19	22	pF

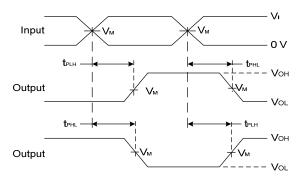
## **Parameter Measurement Information**



V	Inputs			•	1
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	$R_L$
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1ΜΩ



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

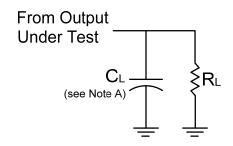
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10MHz
- C. Inputs are measured separately one transition per measurement
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$

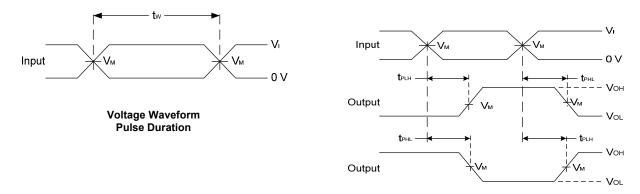
Figure 1 Load Circuit and Voltage Waveforms



## **Parameter Measurement Information (cont.)**



V	Inputs		V	0	
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	$R_L$
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1kΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω



Voltage Waveform Propagation Delay Times
Inverting and Non Inverting Outputs

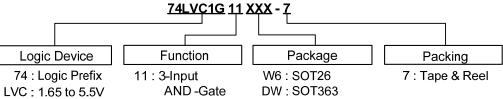
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10MHz
   C. Inputs are measured separately one transition per measurement
- D.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$

Figure 2 Load Circuit and Voltage Waveforms



## **Ordering Information**



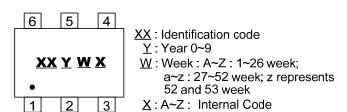
LVC : 1.65 to 5.5V AND -Gate DW : SO 1363
Family FW4 : DFN 1010
1G : One gate FZ4 : DFN 1410

Dout Number	Baskana Cada	Packaging	7" Tape and Reel		
Part Number	Package Code	(Note 7)	Quantity	Part Number Suffix	
74LVC1G11W6-7	W6	SOT26	3000/Tape & Reel	-7	
74LVC1G11DW-7	DW	SOT363	3000/Tape & Reel	-7	
74LVC1G11FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7	
74LVC1G11FZ4-7	FW4	X2-DFN1410-6	5000/Tape & Reel	-7	

Note: 7. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf

## **Marking Information**

### (1) SOT26, SOT363



Part Number	Package	Identification Code
74LVC1G11W6	SOT26	TV
74LVC1G11DW	SOT363	TV

#### (2) X2-DFN1010-6, X2-DFN1410-6

### (Top View)

<u>XX</u> <u>Y **W** X</u>  $\frac{XX}{Y}$ : Identification Code  $\frac{X}{Y}$ : Year : 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week

 $\underline{X}$ : A~Z: Internal code

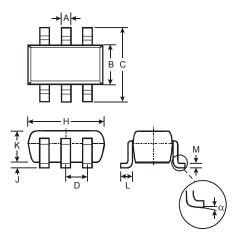
Part Number	Package	Identification Code
74LVC1G11FW4	X2-DFN1010-6	TV
74LVC1G11FZ4	X2-DFN1410-6	TV



## Package Outline Dimensions (All dimensions in mm.)

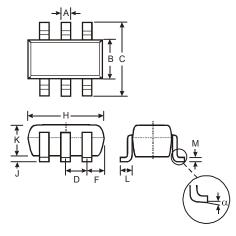
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

### (1) Package Type: SOT26



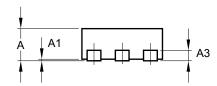
SOT26			
Dim	Min	Max	Тур
Α	0.35	0.50	0.38
В	1.50	1.70	1.60
C	2.70	3.00	2.80
D	_	_	0.95
Н	2.90	3.10	3.00
7	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
М	0.10	0.20	0.15
α	0°	8°	_
All Dimensions in mm			

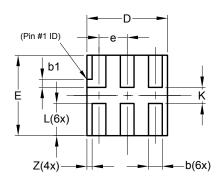
### (2) Package Type: SOT363



	SOT363			
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65	Тур		
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
K	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				

### (3) Package Type: DFN1010





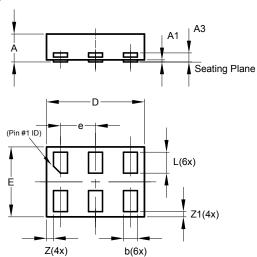
	X2-DFN1010-6			
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
А3			0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е			0.35	
L	0.35	0.45	0.40	
K	0.15	_	_	
Z	_	_	0.065	
All Dimensions in mm				



## Package Outline Dimensions (cont.) (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### (4) Package Type X2-DFN1410-6



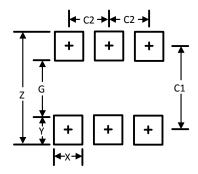
	X2-DFN1410-6			
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
А3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
<b>Z</b> 1	0.045	0.105	0.075	
All Dimensions in mm				



## Suggested Pad Layout (All dimensions in mm.)

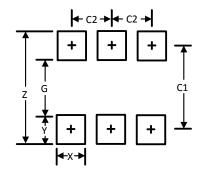
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### (1) Package Type: SOT26



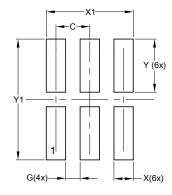
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

### (2) Package Type: SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

### (3) Package Type X2-DFN1010-6



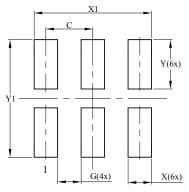
Dimensions	Value
Difficitions	(in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250



#### Suggested Pad Layout (cont.)

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### (4) Package Type: X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

#### **IMPORTANT NOTICE**

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